

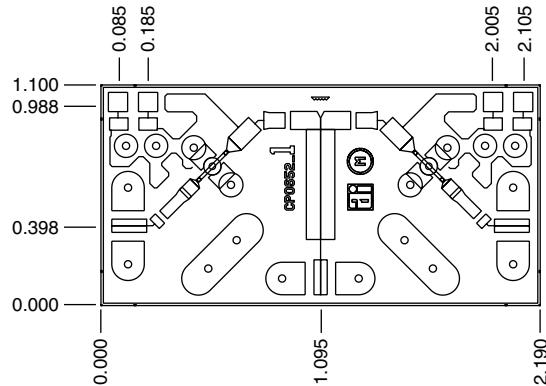
Features

- Broad Bandwidth, 32–45 GHz
- Low Loss, < 1.0 dB
- High Isolation, > 28 dB
- Fast Switching Speed, < 2 ns
- High Power Handling, 37 dBm Peak,
33 dBm CW

Description

Alpha's single pole, double throw PIN diode switch is a robust, high performance switch. It is ideal for low loss, high isolation applications, particularly where broad bandwidths and high power handling is required. The chip uses Alpha's proven PIN diode technology, and is based upon MBE layers for the highest uniformity and repeatability. The diodes employ surface passivation to ensure a rugged, reliable part with through-substrate via holes and gold-based backside metallization to facilitate an epoxy die attach process. The GaAs MMIC employs a shunt PIN diode in each arm and an on-chip bias network. Chips are measured on a 100% basis at 32, 35, 38 and 40 GHz for insertion loss, isolation, input and output return losses and also at DC for diode breakdown voltage and turnon voltage. Characteristics are guaranteed up to 45 GHz.

Chip Outline



Dimensions indicated in mm.
All pads are ≥ 0.07 mm wide.
Chip thickness = 0.1 mm.

Absolute Maximum Ratings

Characteristic	Value
Operating Temperature (T_C)	-55°C to +125°C
Storage Temperature (T_{ST})	-65°C to +150°C
DC Reverse Bias	-70 V (-10 μ A)
DC Forward Bias	+1.3 V (50 mA)
Power In (P_{IN})	10 W

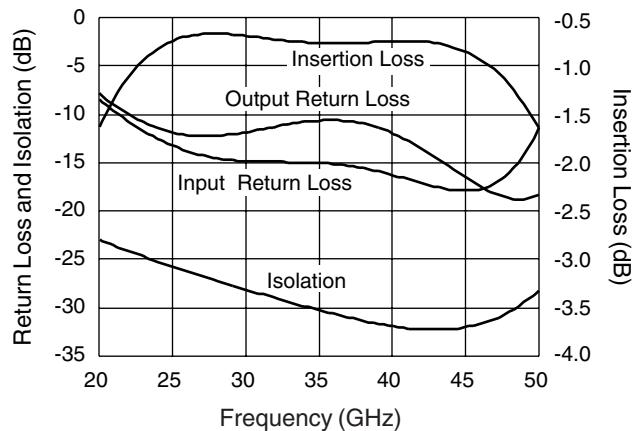
Electrical Specifications at 25°C

Parameter	Condition	Symbol	Min.	Typ. ²	Max.	Unit
Insertion Loss	$F = 32, 35, 38, 40, 45$ GHz	IL		0.8	1.2	dB
Isolation	$F = 32, 35, 38, 40, 45$ GHz	I_{SO}	28	30		dB
Input Return Loss	$F = 32, 35, 38, 40, 45$ GHz	RL_I		14	11	dB
Output Return Loss	$F = 32, 35, 38, 40, 45$ GHz	RL_O		13	10	dB
Leakage Current	$V = -50$ V	I_{DD}		1	10	μ A
Switching Speed ¹				2		ns
Output Power at 1 dB Compression ¹	$F = 35$ GHz	$P_{1\ dB}$		30		dBm
Two-Tone Input Third-Order Intercept ¹	$F = 28$ GHz	$IIP3$	45			dBm

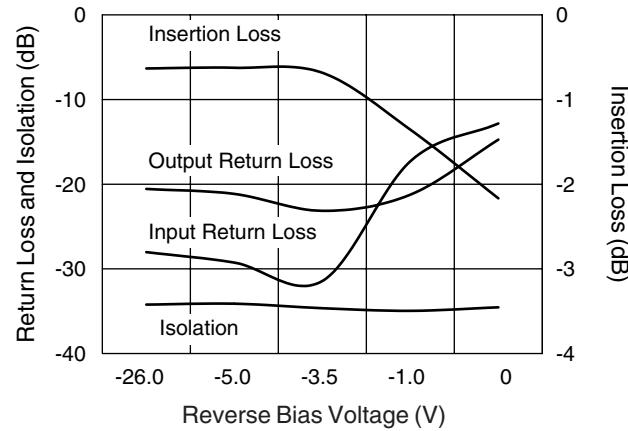
1. Not measured on a 100% basis.

2. Typical represents the median parameter value across the specified frequency range for the median chip.

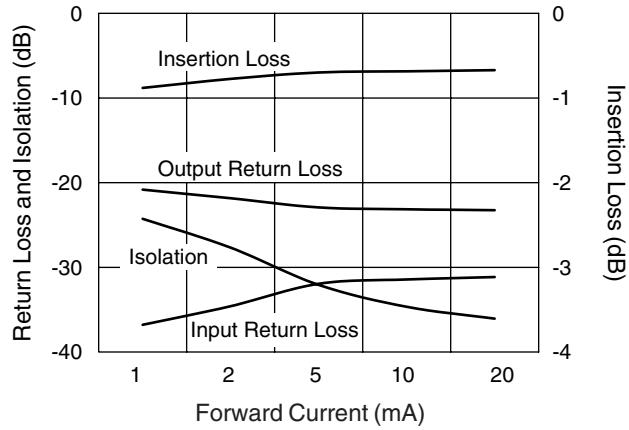
Typical Performance Data



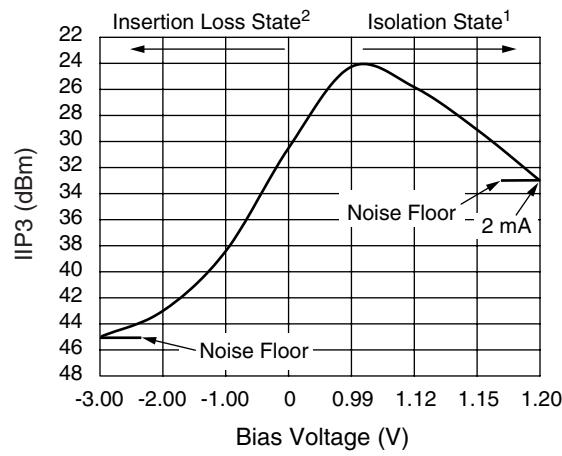
Performance vs. Frequency
Bias Conditions $I_F = 10 \text{ mA}$, $V_R = -5 \text{ V}$



Forward Current
 $F = 28 \text{ GHz}$



$F = 28 \text{ GHz}$, $\text{Reverse Voltage} = -3.5 \text{ V}$



Two-Tone Input Third-Order Intercept @ 28 GHz

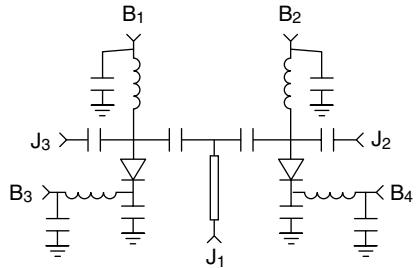
1. Isolation arms are biased with 10 mA (1.25 V) where IIP3 is below the noise floor.

2. Insertion loss arms are biased with -5 V where IIP3 is below the noise floor.

Truth Table

B₁	B₂	J₁–J₂	J₁–J₃
+10 mA	-5 V	Insertion Loss	Isolation
-5 V	+10 mA	Isolation	Insertion Loss

Circuit Schematic



Bias Arrangement

